



N-Channel Enhancement-Mode Vertical DMOS FETs

Features

- ▶ Free from secondary breakdown
- ▶ Low power drive requirement
- ▶ Ease of paralleling
- ▶ Low C_{ISS} and fast switching speeds
- ▶ Excellent thermal stability
- ▶ Integral source-drain diode
- ▶ High input impedance and high gain

Applications

- ▶ Motor controls
- ▶ Converters
- ▶ Amplifiers
- ▶ Switches
- ▶ Power supply circuits
- ▶ Drivers (relays, hammers, solenoids, lamps, memories, displays, bipolar transistors, etc.)

General Description

The Supertex VN2210 is an enhancement-mode (normally-off) transistor that utilizes a vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors, and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Ordering Information

Device	Package Options		Wafer / Die Options		
	TO-39	TO-92	NW (Die in wafer form)	NJ (Die on adhesive tape)	ND (Die in wafer pack)
VN2210	VN2210N2	VN2210N3-G	VN5210NW	VN5210NJ	VN5210ND

For packaged products, -G indicates package is RoHS compliant ('Green'). TO-39 package is RoHS compliant ('Green').
 Devices in Wafer / Die form are RoHS compliant ('Green').
 Refer to Die Specification VF52 for layout and dimensions.

Product Summary

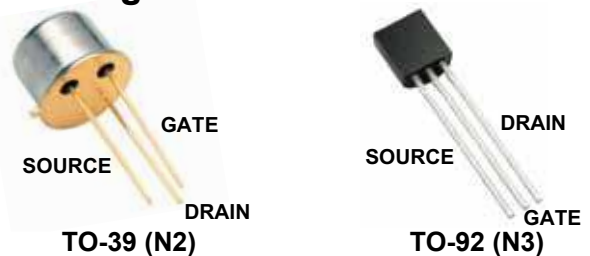
BV_{DSS}/BV_{DGS} (V)	$R_{DS(ON)}$ (max) (Ω)	$I_{D(ON)}$ (min) (A)
100	0.35	8.0

Absolute Maximum Ratings

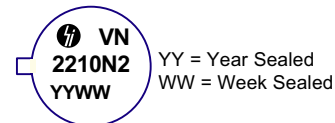
Parameter	Value
Drain-to-source voltage	BV_{DSS}
Drain-to-gate voltage	BV_{DGS}
Gate-to-source voltage	$\pm 20V$
Operating and storage temperature	-55°C to +150°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

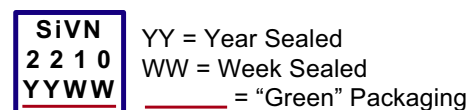
Pin Configurations



Product Marking



Package may or may not include the following marks: Si or **TO-39 (N2)**



Package may or may not include the following marks: Si or **TO-92 (N3)**

Thermal Characteristics

Package	I_D (continuous) [†] (A)	I_D (pulsed) (A)	Power Dissipation @ $T_c = 25^\circ\text{C}$ (W)	θ_{JC} ($^\circ\text{C}/\text{W}$)	θ_{JA} ($^\circ\text{C}/\text{W}$)	I_{DR} [†] (A)	I_{DRM} (A)
TO-39	1.7	10	6.0	21	125	1.7	10
TO-92	1.2	8.0	1.0	125	170	1.2	8.0

Notes:

[†] I_D (continuous) is limited by max rated T_j .

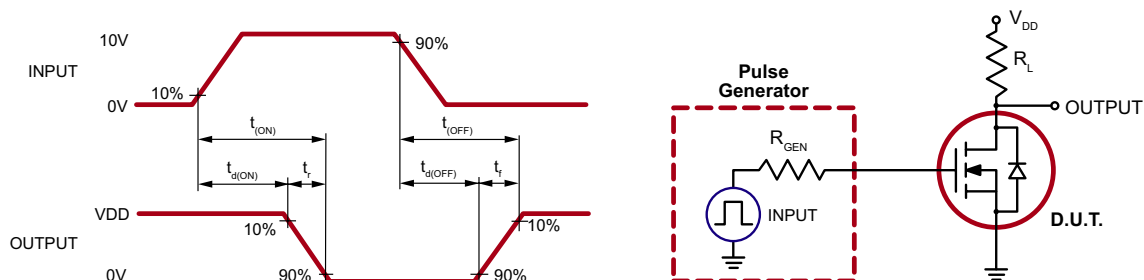
Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Sym	Parameter	Min	Typ	Max	Units	Conditions
BV_{DSS}	Drain-to-source breakdown voltage	100	-	-	V	$V_{GS} = 0V, I_D = 10\text{mA}$
$V_{GS(th)}$	Gate threshold voltage	0.8	-	2.4	V	$V_{GS} = V_{DS}, I_D = 10\text{mA}$
$\Delta V_{GS(th)}$	Change in $V_{GS(th)}$ with temperature	-	-4.3	-5.5	mV/ $^\circ\text{C}$	$V_{GS} = V_{DS}, I_D = 10\text{mA}$
I_{GSS}	Gate body leakage current	-	-	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
I_{DSS}	Zero gate voltage drain current	-	-	50	μA	$V_{GS} = 0V, V_{DS} = \text{Max Rating}$
		-	-	10	mA	$V_{DS} = 0.8 \text{ Max Rating}, V_{GS} = 0V, T_A = 125^\circ\text{C}$
$I_{D(ON)}$	On-state drain current	3.0	4.5	-	A	$V_{GS} = 5.0V, V_{DS} = 25V$
		8.0	17	-		$V_{GS} = 10V, V_{DS} = 25V$
$R_{DS(ON)}$	Static drain-to-source on-state resistance	-	0.4	0.5	Ω	$V_{GS} = 5.0V, I_D = 1.0A$
		-	0.27	0.35		$V_{GS} = 10V, I_D = 4.0A$
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with temperature	-	0.85	1.2	%/ $^\circ\text{C}$	$V_{GS} = 10V, I_D = 4.0A$
G_{FS}	Forward transconductance	1200	-	-	mmho	$V_{DS} = 25V, I_D = 2.0A$
C_{ISS}	Input capacitance	-	300	500	pF	$V_{GS} = 0V, V_{DS} = 25V, f = 1.0\text{MHz}$
C_{OSS}	Common source output capacitance	-	125	200		
C_{RSS}	Reverse transfer capacitance	-	50	65		
$t_{d(ON)}$	Turn-on time	-	10	15	ns	$V_{DD} = 25V, I_D = 2.0A, R_{GEN} = 10\Omega$
t_r	Rise time	-	10	15		
$t_{d(OFF)}$	Turn-off time	-	50	65		
t_f	Fall time	-	30	50		
V_{SD}	Diode forward voltage drop	-	1.0	1.6	V	$V_{GS} = 0V, I_{SD} = 4.0A$
t_{rr}	Reverse recovery time	-	500	-	ns	$V_{GS} = 0V, I_{SD} = 1.0A$

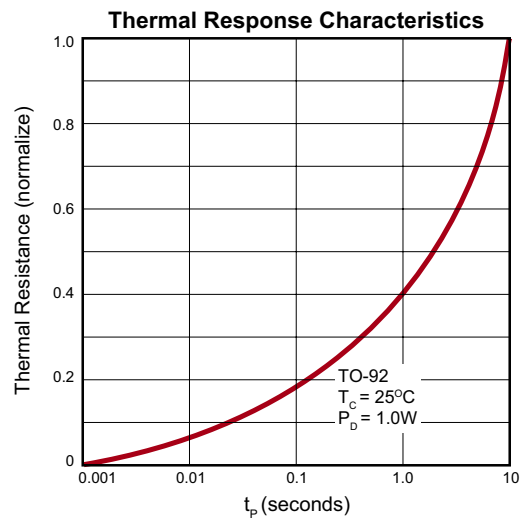
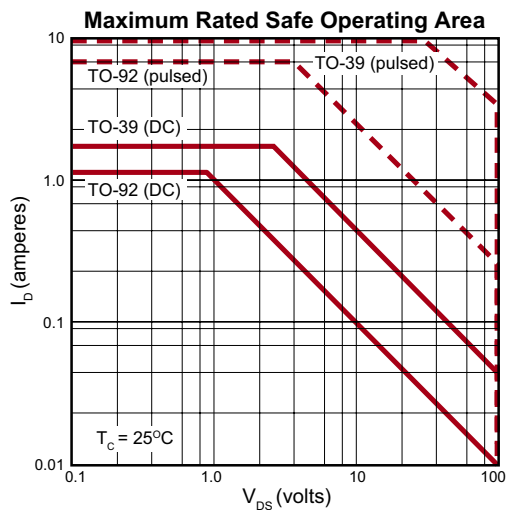
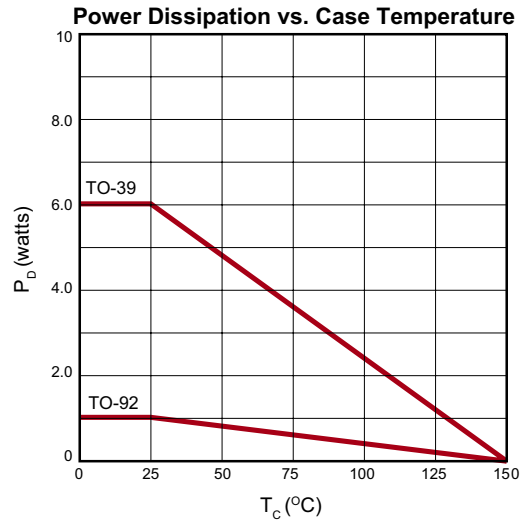
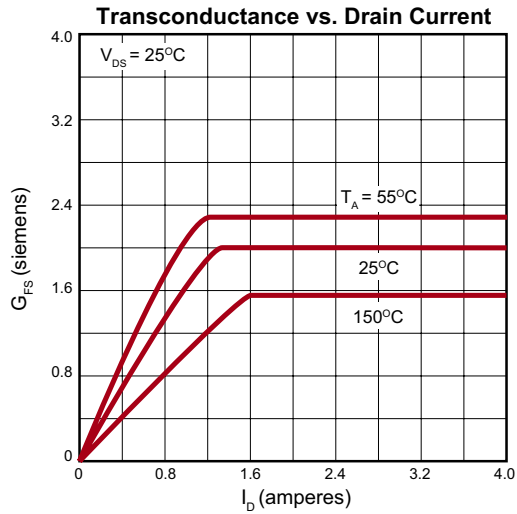
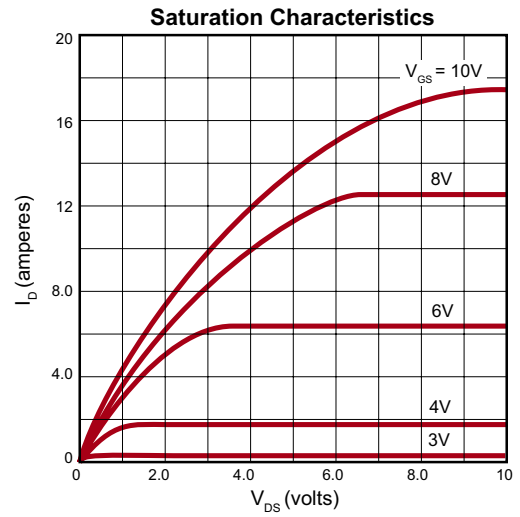
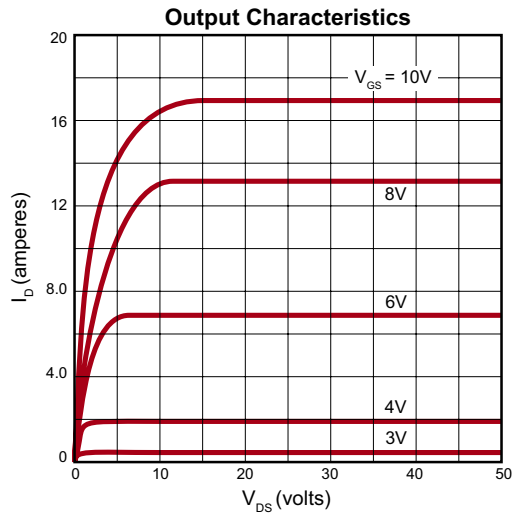
Notes:

- All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: $300\mu\text{s}$ pulse, 2% duty cycle.)
- All A.C. parameters sample tested.

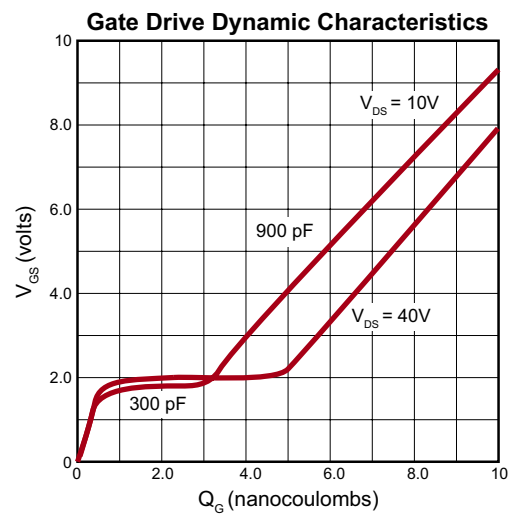
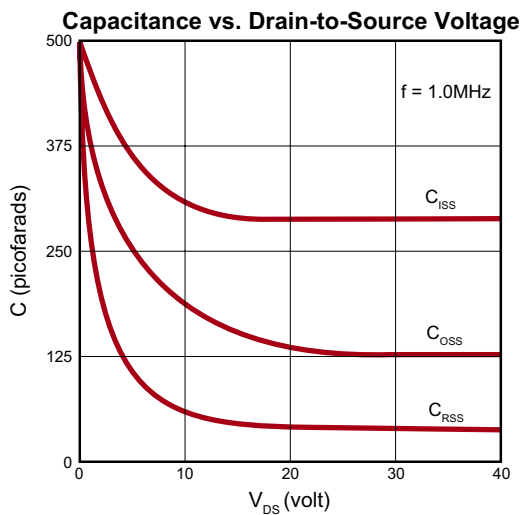
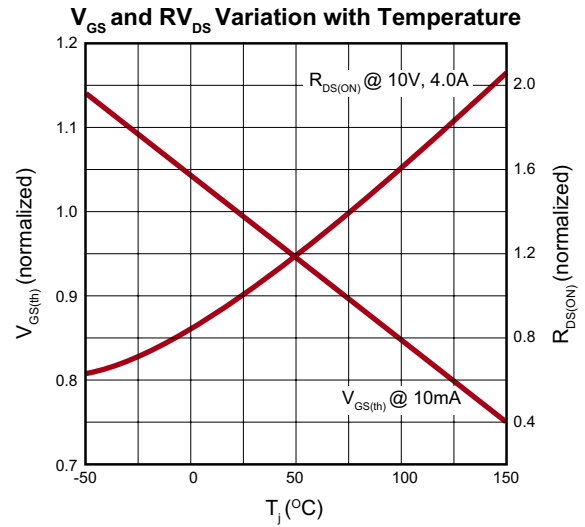
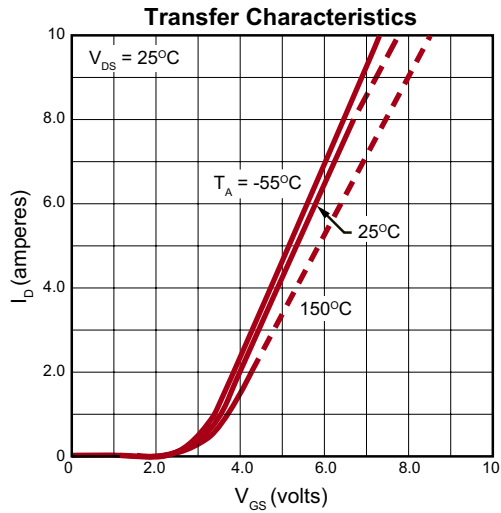
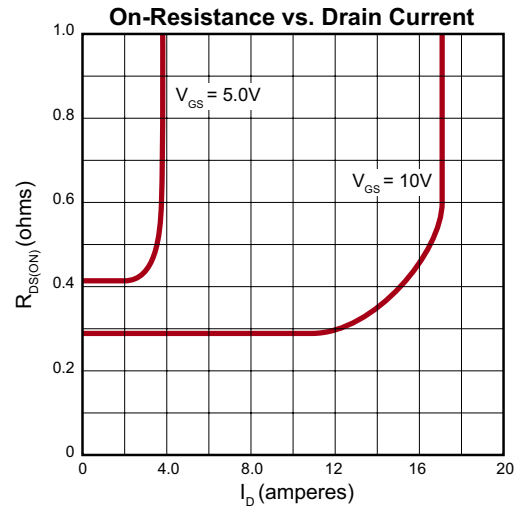
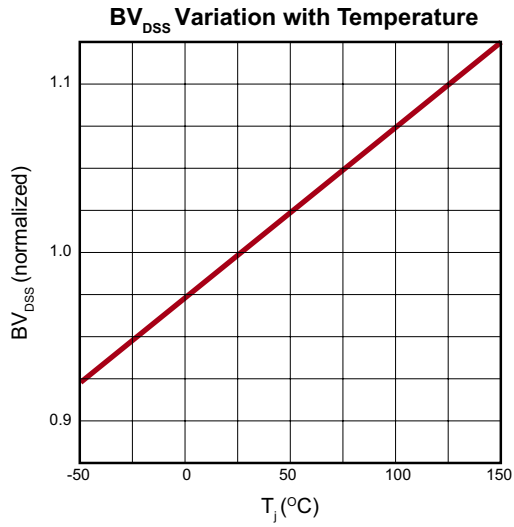
Switching Waveforms and Test Circuit



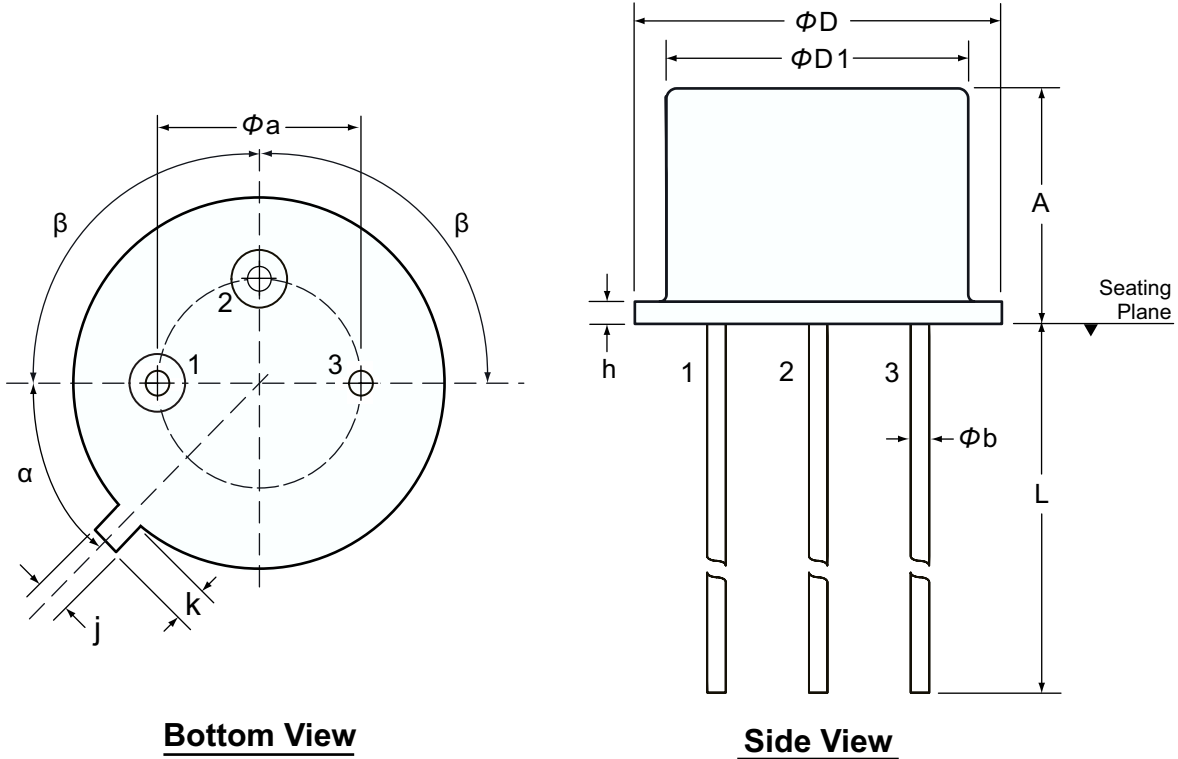
Typical Performance Curves



Typical Performance Curves (cont.)



3-Lead TO-39 Package Outline (N2)



Bottom View

Side View

Symbol	α	β	A	ϕ_a	ϕ_b	ϕ_D	ϕ_{D1}	h	j	k	L	
Dimension (inches)	MIN	45° NOM	90° NOM	.240	.190	.016	.350	.315	.009	.028	.029	.500
	NOM			-	-	-	-	-	-	-	-	-
	MAX			.260	.210	.021	.370	.335	.125	.034	.040	.560*

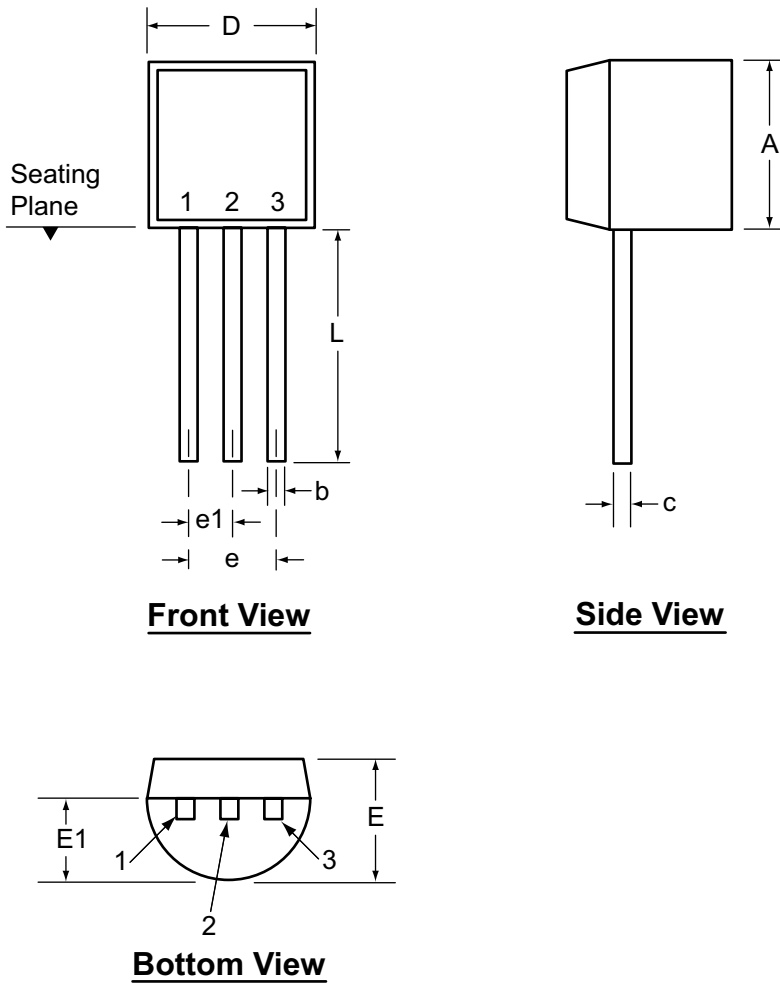
JEDEC Registration TO-39.

* This dimension is not specified in the JEDEC drawing.

Drawings not to scale.

Supertex Doc. #: DSPD-3TO39N2, Version B052009.

3-Lead TO-92 Package Outline (N3)



Symbol	A	b	c	D	E	E1	e	e1	L
Dimensions (inches)	MIN	.170	.014†	.175	.125	.080	.095	.045	.500
	NOM	-	-	-	-	-	-	-	-
	MAX	.210	.022†	.022†	.205	.165	.105	.105	.610*

JEDEC Registration TO-92.

* This dimension is not specified in the JEDEC drawing.

† This dimension differs from the JEDEC drawing.

Drawings not to scale.

Supertex Doc.#: DSPD-3TO92N3, Version E041009.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to <http://www.supertex.com/packaging.html>.)

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